

## SILICON BRIDGE RECTIFIER

VOLTAGE RANGE: 1200 V

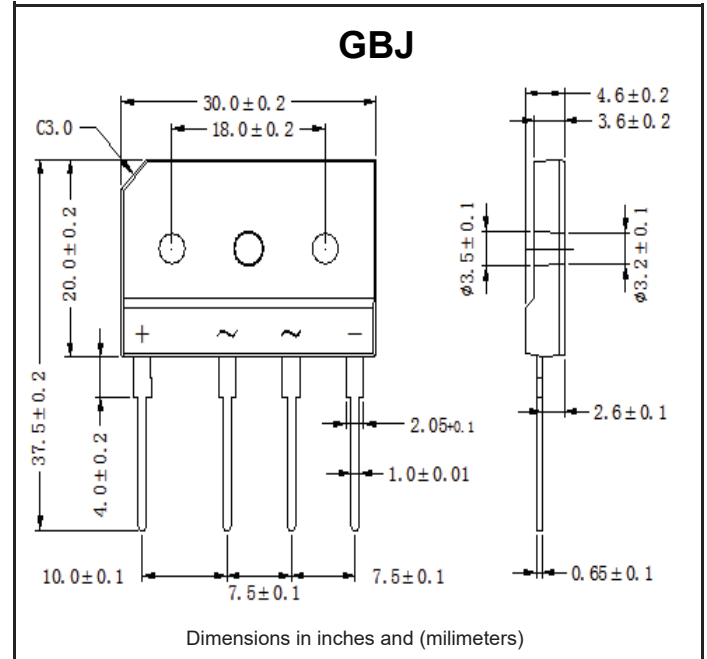
CURRENT: 25.0 A

### FEATURES

- Rating to 1000V PRV
- Ideal for printed circuit board
- Low forward voltage drop, high current capability
- Reliable low cost construction utilizing molded plastic technique results in inexpensive product
- The plastic material has UL flammability classification 94V-0
- Weight: 0.24 ounces, 6.79grams

### MECHANICAL DATA

- Polarity: Symbols molded on body
- Weight: 0.23 ounces, 6.6 grams
- Mounting position: Any



## MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted) Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate by 20%.

CHARACTERISTICS	SYMBOL	GBJ 2512	UNIT
Maximum Recurrent Peak Reverse Voltage	VRRM	1200	V
Maximum RMS Voltage	VRMS	840	V
Maximum DC Blocking Voltage	VDC	1200	V
Maximum Average Forward Rectified Current @ Tc=100°C (without heatsink)	I(AV)	25.0 3.5	A
Peak Forward Surge Current 8.3ms Single Half Sine-Wave Super Imposed on Rated Load (JEDEC Method)	IFSM	350	A
Maximum Forward Voltage at 12.5A DC	VF	1.1	V
Maximum DC Reverse Current at Rated DC Blocking Voltage	IR	10 500	uA
Typical Thermal Resistance (Note2)	RθJC	1.0	°C/W
Operating Temperature Range	TJ	-55 to +150	°C
Storage Temperature Range	TSTG	-55 to +150	°C

NOTES: 1. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.  
2. Device mounted on 300mm\*300mm\*1.6mm cu plate heatsink.

# RATINGS AND CHARACTERISTIC CURVES

FIG.1-FORWARD CURRENT DERATING CURVE

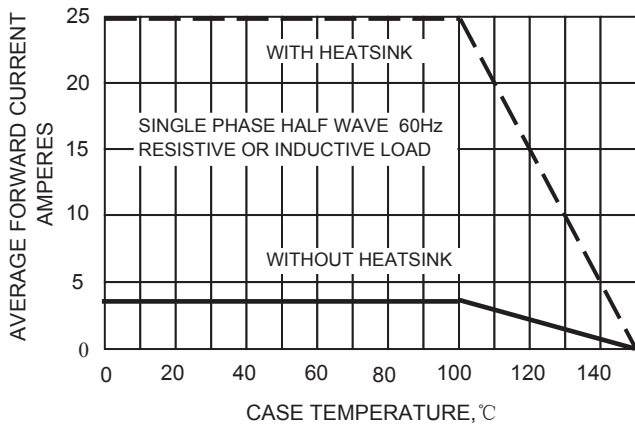


FIG.2-MAXMUN NON-REPETITIVE SURGE CURRENT

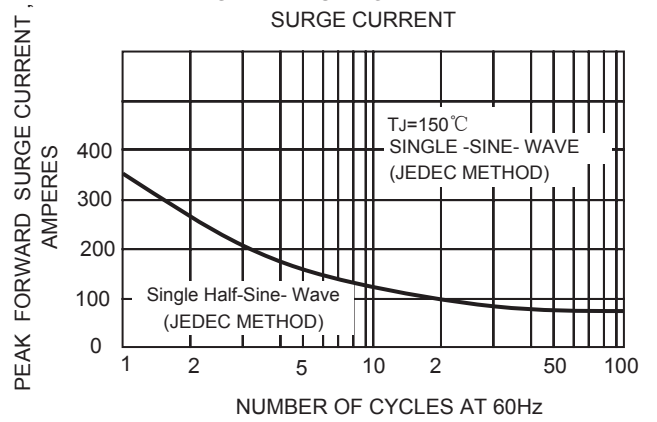


FIG.3-TYPICAL JUNCTION CAPACITANCE

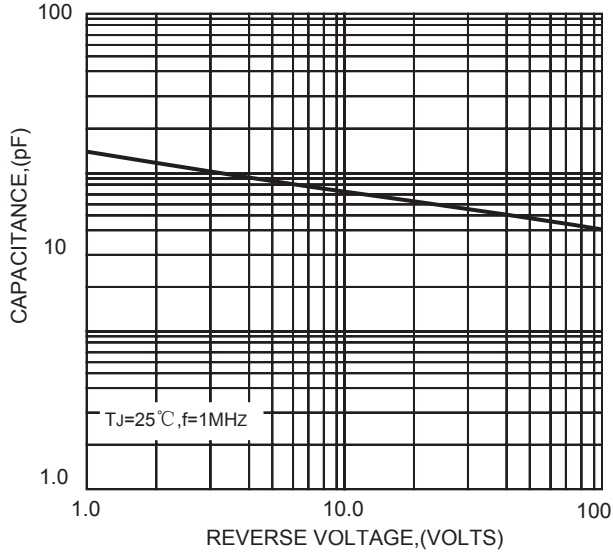


FIG.4-TYPICAL FORWARD CHARACTERISTICS

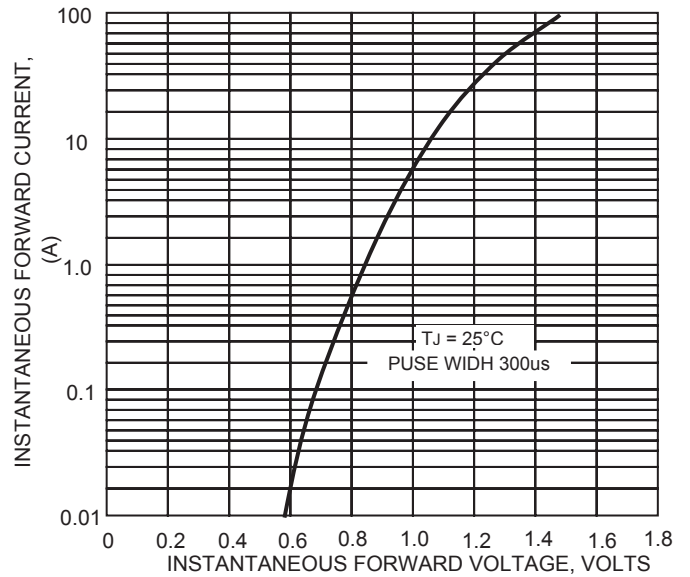


FIG.5-TYPICAL REVERSE

